Amendments to the Claims

Claims 1-15 (*Cancelled*)

16. (*Currently Amended*) A method of manufacturing a ferroelectric device ~~as claimed in claim 1~~,

_____wherein a body is formed that comprises a substrate, and the device is provided with a ferroelectric layer ~~provided with~~ having a connection conductor on a side facing away from the substrate,

_____an oxygen-free ferroelectric material being selected as the material for the ferroelectric layer which is used to form an active electrical element, characterized in that a conductive layer is provided between the substrate and the ferroelectric layer,

_____which conductive layer forms a further connection conductor of the ferroelectric layer, and

_____the memory element is obtained by forming a Schottky junction between the ferroelectric layer and at least one of the connection conductors.

17. (*Previously Presented*) A method according to claim 16, characterized in that the active electrical element is formed as a memory element.

18. (*Previously Presented*) A method as claimed in claim 17, characterized in that the body is formed so as to be a semiconductor body, and a semiconductor substrate is selected as the substrate.

19. (*Previously Presented*) A method as claimed in claim 17, characterized in that in the semiconductor body there is formed a field effect transistor with a source region, a drain region and a gate electrode, and the further connection conductor is provided on the source or drain region of the field effect transistor and is formed so as to be a connection conductor of the source region or drain region.

20. (*Previously Presented*) A method as claimed in claim 17, characterized in that the Schottky junction is formed between the further connection conductor and the ferroelectric layer, and an ohmic contact is formed between the connection conductor and the ferroelectric layer as well as between the further connection conductor and the source or drain region of the field effect transistor.

21. (*Previously Presented*) A method as claimed in claim 17, characterized in that the ferroelectric layer is formed by converting part of a conductive layer to the ferroelectric material, one of the connection conductors being formed by the remaining part of the conductive layer.

22. (*Previously Presented*) A method as claimed in claim 17, characterized in that a matrix of N x M memory elements is formed, where N and M are natural numbers and each memory element is provided on both sides with an electric connection.

23. (*Previously Presented*) A method as claimed in claim 22, characterized in that each memory element is coupled to a field effect transistor formed in the device and associated with said memory element, which field effect transistor comprises a source region, a drain region and a gate electrode, and the device is provided with N first conductor tracks, M second conductor tracks and with a ground connection, and each memory element is connected via the connection conductor to one of the N first conductor tracks and via the further connection conductor to the source or drain region of the associated field effect transistor , of which the other drain or source region is connected to the ground connection , while the gate electrode is connected to one of the M second conductor tracks .

24. (*Previously Presented*) Method of operating a ferroelectric device as claimed in claim 15, characterized in that the ferroelectric device is operated outside the voltage region where the ferroelectric memory effect occurs.